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Author Poirot, I.

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I. Poirot, W. Kot, G. Shalimoff, N. Edelstein, M.M. Abraham, C.B. Finch, and L.A. Boatner

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Optical and EPR Investigations of Np^{4+} in Single Crystals of ZrSiO₁₁

I. Poirot, W. Kot, G. Shalimoff, N. Edelstein Materials and Chemical Sciences Division Lawrence Berkeley Laboratory and Department of Chemistry University of California Berkeley, California 94720

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and

M.M. Abraham, C.B. Finch, L.A. Boatner Solid State Division Oak Ridge National Laboratory* Oak Ridge, TN 37831

ABSTRACT

Polarized optical spectroscopy has been used to investigate the electronic structure of tetravalent neptunium incorporated as a-dilute impurity in single crystals of the tetragonal host $2rSiO_{\mu}$. Thirty-one levels were assigned from 30 intense polarized optical transitions and used in obtaining a fit to a parametric Hamiltonian to within an rms deviation of 34 cm^{-1} . Thirteen other levels with comparable intensities and good polarization characteristics were observed. An inclusion of these levels using the parameters from the 31 level fit, however, resulted in an increase of the rms deviation to approximately 100 cm^{-1} .

Operated by Martin Marietta Energy Systems, Inc. for the U.S. Department of Energy under contract DE-AC05-840R21400.

The EPR spectra of the ground state of NP^{4+} :ZrSiO_n were measured and fit to an axial spin Hamiltonian to obtain the parameters: $|g_{||}| = 0.8 \pm$ 0.6, $|g|$ = 2.59 ± 0.02, A = -2400 ± 1200 MHz, and B = 4750 ± 30 MHz. These results are consistent with the calculated r_6 ground state.

I. Introduction

Investigations of the optical spectra of tetravalent neptunium incorporated as a dilute impurity in the single crystal hosts ThO₂ and PbMoO_n were first reported in 1969.^{1,2} Subsequently, optical spectroscopic studies of Np ⁴⁺ in the host single crystal CsNpCl₆ were carried out.³ In all of these early investigations, assignments were only made to the low-lying levels of Np^{4+} . More recently, optical spectroscopic investigations of Np^{4+} doped into two additional host single crystals have been reported.^{4,5} Tetravalent neptunium has been studied as a dilute impurity in Zr(BD₁₁)₁ and 46 levels were assigned in the spectrum and fit to a parametric Hamiltonian with an rms deviation $\sigma = 84$ cm⁻¹.⁴ Np⁴⁺ has also been investigated as an impurity in single crystals of the zircon structure host $ThSiO_{\mu}$. In this case, 29 levels were assigned in the observed spectrum and these levels were fit with an rms deviation σ = 47 cm $^{-1}$.⁵ In the present work, optical spectroscopy has been used to investigate Np⁴⁺ in single crystals of ZrSiO_n. The observed optical transitions were assigned and used in obtaining fits to a parametric Hamiltonian. Addtionally, Electron Paramagnetic Resonance (EPR) spectroscopy has been used to study the Np^{4+} ground state in zirconium silicate.

II. Experimental

A. Optical Measurements

Single crystals of ZrSiO_{μ} doped with Np⁴⁺ were grown in platinum crucibles in air using a $Li₂0.6$ MoO₃ flux. After heating the crystal growth charge to 1350°C, the growth furnace was slowly cooled (at about 1°C/h) to 950°C. The crystal growth procedures have been described in detail elsewhere. $6-8$ Crystal growth runs were carried out with doping levels of 0.2 wt.% Np and 2.0 wt.% Np relative to $ZrSiO_{\mu}$. Single crystals of $ZrSiO_{\mu}$ grown with the lower Np doping were well formed and transparent, and a specimen $-2 \times 2 \times 2$ mm³ was selected for use in the optical spectroscopic investigations. In the case of the ZrSiO₁, crystals with the higher neptunium doping, although the crystals were larger relative to the lightly doped samples, they exhibited a green color and contained inclusions. Accordingly, it was necessary to prepare the optical samples by cutting thin (-0.5 mm) sections with known orientations from the larger "as grown" crystals. The two types of crystals were mounted on slotted copper plates with their optical axis either perpendicular or parallel to the slit, and then sealed in quartz tubes containing a partial pressure of helium gas.

The Np concentration for both doping levels was determined by Y-ray counting methods. The Np decay (Eq. 1)

$$
{}^{237}_{93}Np \xrightarrow{0}{-} {}^{233}_{2.14\times10} {}^{6}_{y} \xrightarrow{91} {}^{233}_{27}Pa \xrightarrow{0}{-} {}^{233}_{27}U \xrightarrow{0}{-} {}^{233}_{92}U \xrightarrow{0}{-} {}^{24}_{1.62\times10} {}^{5}_{y} \tag{1}
$$

was at equilibrium in these crystals, and the relative intensities of the spectra of multiple Y and x-ray lines of Pa, U, and Np were compared to a reference with the same geometry (i.e., 1 mg of dissolved Np

evaporated on a copper plate and sealed in glass tubing). The high energy (100 to 340 keV) γ and x-ray lines of 233 Pa, which were unaffected by the glass tubing and the crystal, gave measured Np concentrations of approximately 0.1 and 1.0 wt. $%$ for the low and high doping levels of Np in $ZrSiO_{\mu}$, respectively.

The optical absorption spectra for both σ and π polarizations were recorded between 20000A and 3500A at room, liquid N_2 , and liquid He temperatures (see Figs. 1 and 2) using a Cary 17 spectrophotometer. In addition, absorption spectra in the 7600-3500A range were taken at 4.2K with Jarrell-Ash F6 and 3.4 m-spectrographs. At liquid helium temperature, the observed line widths varied between 15 and 70 cm^{-1} with the average value being approximately 30 cm^{-1} . Attempts were made to obtain the Zeeman spectra in a magnetic field of 2.7 T at $4.2K$ with the magnetic field applied parallel and perpendicular to the optical axis, but no line broadening or splittings were observed. Additionally, no fluorescence was observed in the visible and near IR regions and no electronic Raman spectra were detected at 4.2K for either crystal.

B. EPR Measurements

EPR spectra were obtained at $4.2K$ and 35 GHz using a Varian E110 microwave resonance spectrometer with an electromagnet that could be rotated about the vertical axis. The maximum obtainable magnetic field was 16 kG. The magnetic-field positions of the EPR transitions were measured by proton NMR, and the microwave frequency was determined with an EIP frequency counter.

A single crystal of Np doped ZrSiO_{μ} was selected and oriented in the cylindrical 35 GHz cavity (TE₀₁₁) so that the applied magnetic field

could be rotated in the ac crystallographic plane. All six hyperfine lines for the $I=5/2$ ²³⁷Np isotope were observed with \vec{H} perpendicular to the c-axis of the crystal. These lines moved to higher field values as the field orientation was rotated toward the crystal c-axis. Magneticfield positions were recorded as a function of the magnetic-field orientation at angles where at least three hyperfine lines could be observed (the other lines having shifted above the range of the magnetic field). This corresponded to a rotation of approximately \pm 50° about the direction perpendicular to the c-axis. Additionally, because of problems in positioning the crystal that was encapsulated in polyethylene tubing in the microwave cavity, a \pm 10° uncertainty is estimated in the orientation of the plane of magnetic-field rotation relative to the ac plane of the $ZrSiO_µ$ crystal.

III. Optical Results

The optical absorption results obtained as described in Sec. II-A above can be divided into six groups of transitions. Table I lists the wavelengths for the transitions observed with both the dilute and concentrated Np^{4+} doped ZrSiO_h single crystals along with the polarization characteristics, intensities, and assignments for the" transitions. The features and details of the six groups of optical transitions are described in the following section.

A. First Group (5000-6000 cm^{-1} , 20000-15000A)(Fig. 1)

Six absorption bands appeared in this range in $ZrSiO_{\mu}$ crystals with both Np⁴⁺ doping levels. These features became better resolved as the crystals were cooled. Five of the bands showed strong σ or π

polarization and could be assigned to transitions from a Γ_6 ground state to a higher lying Γ_6 or Γ_7 level based on the polarization characteristics. Only a few of the bands exhibited the expected polarization extinction. Generally, the π absorption lines were not accompanied by a σ transition (at 5514, 6072, 6096 $\rm cm^{-1}$) as permitted by the selection rules. This clearly isolated group was assigned to the $^{\frac{11}{11112}}$ multiplet. Six stark levels, three r_6 and three r_7 , result from the crystal field interaction. The 17470 ± 10 A band must be attributed to a transition to a Γ_6 level even though a very weak and broad absorption appears with π polarization.

The weak, broad absorption at about 19350A was only observed at room temperature and gave an indication of the ground term splitting. This peak is separated by 350 cm^{-1} from the 5515 cm^{-1} transition. It has the same π polarization and resulted from the partial population of the first excited Γ_6 level of the $\frac{4}{9/2}$ manifold at room temperature.

Some other broad, weak lines and shoulders were observed, but they could not be assigned. These features may be due to electronic plus vibronic excitations. Furthermore, particularly in this group, the heavily doped $2rSiO_{\mu}$ crystal showed additional absorption lines as compared to the more dilute crystal. These extra lines were strongly polarized and indicate that an additional site may be present at higher Np concentration levels.

B. Second Group (8300-8400 cm^{-1} , 12500-11500A)(Fig. 1)

Two absorption lines are observed in this range and these were assigned to the ${}^{4}F_{3/2}$ state that is split into Γ_6 and Γ_7 levels. Again the Γ_6 to Γ_7 transition is intense for π polarization (at 12000A) for

both Np concentrations, but is very weak in σ polarization, and in fact, is barely visible in the dilute Np-doped crystal.

<u>C. Third Group (9600-12600 cm⁻¹, 10500-7900A) (Fig. 1)</u>

According to preliminary calculations (See Sec. IV-A), the $J =$ *13/2, 912* (II) and *5/2* (I) manifolds are expected to be found in this group. At this point, however, it was difficult to classify the individual J states for the 14 absorption bands detected in this range. Nine lines in this region could be identified as Γ_6 or Γ_7 crystal field levels according to their polarization characteristics. As in the case of the first group, a weak, broad line at 9660 cm^{-1} was found about 350 cm^{-1} from the next intense transition, and this line was detected only at room temperature. This temperature-dependent line confirmed the assignment of the first excited state at 350 cm⁻¹.

D. Fourth Group (13200-16085 cm⁻¹, 7800-6100A)(Fig. 2)

A difference of only 650 cm⁻¹ separated this group from the third group of transitions. Because of J mixing by the crystal field, some overlap may occur between this group and the lower energy one. Nevertheless, assuming that the J levels are relatively isolated, levels derived from the J = 5/2(11), 3/2(11), *7/2(1),* and *15/2(1)* are expected. Nine of the observed 14 bands in this group could be assigned from their polarization characteristics.

E. Fifth Group (16495-16640 cm⁻¹, ~6000A)(Fig. 2)

Only two transitions appeared in this group that were separated from the other groups. As in other compounds of Np^4 +, these transitions

can be attributed to the ${}^{4}G_{7/2}$ manifold. One transition is strongly π polarized (Γ_7) and the other is strongly σ polarized (Γ_6) .

F. Sixth Group (17600-28800 cm-1, 5800-3500A) (Fig. 2) **•**

This group represents the highest energy part of the spectrum, and it was relatively complex. Fourteen intense lines could be identified as Γ_6 or Γ_7 , however, from their strongly polarized transitions.

IV. Optical Data Analysis

A. Energy Level Assignments

The energy levels within an f^n configuration in D_{2d} symmetry can be written in terms of the free-ion (H_{FT}) and crystal-field (H_{CF}) Hamiltonians as follows: $9-11$

$$
H_{FI} = \sum_{k=0,2,4,6} F^{k}(nf, nf) f_{k} + \zeta_{f} a_{s0} + \alpha L(L + 1)
$$
 (2)
+ $\beta G(G_{2}) + \gamma (R_{7}) + \sum_{k=0,2,4} M^{k} m_{k} + \sum_{2,4,6} P^{k} p_{k}$

and

$$
H_{CF} = B_0^2 C_0^2 + B_0^4 C_0^4 + B_4^4 (C_4^4 + C_{-4}^4)
$$
 (3)

$$
+ B_0^6 c_0^6 + B_4^6 (c_4^6 + c_{-4}^6).
$$

The F^K (nf,nf)'s and ζ_f above represent the radial parts of the electrostatic and spin-orbit interactions, respectively, between f electrons, while f_k and a_{s0} are angular parts of these interactions.

The parameters α , β , and γ are associated with the two-body effective operators of the configuration interaction. The M^k parameters represent the spin-spin and spin-other-orbit interactions while the P^{k} parameters arise from electrostatic-spin-orbit interactions with higher configurations. The crystal field interaction for D_{2d} symmetry is parameterized by B_0^2 , B_0^4 , B_4^4 , B_0^6 , and B_4^6 , and the angular operators $C_q^{(k)}$ are the usual Racah tensors.

For an odd number of electrons (as in Np^{4+} , 5f³) in D_{2d} symmetry, the Kramers degenerate states are classified by the r_{6} and r_{7} double group representations. The selection rules for the allowed electricdipole transitions in this symmetry are given in Table II. In ZiSiO₁, crystals containing Np^{4+} at both doping levels, the absorption spectra did not precisely follow the expected polarization. This effect will be described more fully later.

The optical spectra of $\texttt{U}^{\natural +}$ doped into both ZrSiO₄ and ThSiO₄ single crystals have previously been studied. $12-14$ Although these two host crystals are isostructural as noted above, the size of the positive metal ions $2r^{4+}$ and Th⁴⁺ is quite different. This size difference results in a crystal field whose strength is very different for the two crystals at the site of an impurity ion such as U^{4+} or Np^{4+} . Accordingly, the spectra of U^{4+} :ThSiO₁ and U^{4+} :ZrSiO₁ differ quite markedly. (It is interesting to note that the resemblance of the spectrum of u^{4+} :ThSiO₄ to that of u^{4+} :ThBr₄ has recently led to a reanalysis of the data for these systems.¹⁴) Nevertheless it is expected that the crystal-field parameters will not vary greatly for two consecutive ions in the periodic table (the only difference being in the number of f electrons) in the same host crystal. This premise is

exploited in carrying out the analysis of the optical spectrum of $NP^{4+}:ZrSiO_{\mu}$ in the present work.

A preliminary calculation was performed using the free-ion parameters obtained from the analysis of the optical results of either NP^{4+} :Zr(BD_H)_H⁴ or Np⁴⁺:ThSiO_H⁵ along with the crystal-field parameters obtained from the analysis of the data for $\texttt{U}^{\natural+};$ ZrSiO $_\texttt{u}$. These calculations predicted a Γ_{6} ground state that is well separated from the higher energy levels as well as relatively isolated J levels for those whose energy was less than $~10000~cm^{-1}$.

B. Parametric Fit of the Optical Data

From the calculated energy levels, 30 transitions could be assigned for which there was good agreement between the calculated and measured energies along with consistency for the polarization characteristics and with the expected eigenvector composition. The free-ion parameters F^2 , F^4 , F^6 , and ζ were varied with the crystal-field parameters fixed at the u^{4+} :ZrSiO_n values. The crystal-field parameters were then allowed to vary with the free-ion parameters fixed, and finally, all of the above parameters were varied simultaneously. The remaining parameters were fixed at the values used for Np^{4+} :Zr(BD₄)₄. For the fit with 31 levels, an rms deviation of 34 $\rm cm^{-1}$ was obtained.

Thirteen additional transitions were present that, together with the 30 transitions discussed above, correspond to the strongest observed transitions. The addition of these 13 transitions resulted in some interchanges in the r_6 and r_7 levels in the calculated spectrum. Furthermore, fitting these additional levels did not significantly improve the rms deviation obtained by using the parameters resulting

from the 31 level fit when the extra 13 transitions were assigned to the nearest calculated energy level of the correct symmetry.

The final values of the parameters obtained with the 31 level fit are given in Table V and this fit resulted in an rms deviation of σ = 34 cm⁻¹ as noted above (varying 12 parameters including α and β). For the fit with 44 levels a value for σ of 103 cm⁻¹ was obtained. The calculated energy levels and eigenvectors are given in Table VI .

. V. EPR Ground State Data and Analysis

 \bullet

The EPR line positions obtained as a function of the applied magnetic-field orientation were fitted to the parameters of the axial spin-Hamiltonian¹⁵

$$
\mathcal{H} = g_{\parallel} \mu_{B} H_{Z} S_{Z} + g_{\perp} \mu_{B} (H_{x} S_{x} + H_{y} S_{y})
$$
\n
$$
+ A_{\parallel} S_{Z} I_{Z} + A_{\parallel} (S_{x} I_{x} + S_{y} I_{y})
$$
\n(4)

where $\mu_{\mathbf{p}}$ is the Bohr magneton and H is the magnetic field. The other parameters have their usual meaning. Due to the small value of g_{\parallel} and the problems with the orientation of the crystal, the uncertainties in the values of $g_{||}$ and A are much greater than the errors in $g_{||}$ and B. The resulting parameters for the spin-Hamiltonian are given in Table III. An additional analysis was attempted in which a quadrupolar term was added to the spin-Hamiltonian, but this refinement did not significantly improve the fit. The data given in Table III are consistent with the calculated Γ_{6} calculated ground state and serve to confirm that assignment.

For a pure J state, the ratio of a/g , A/g_{\parallel} , and B/g_{\parallel} should be constant, (where a and g are, respectively, the hyperfine coupling constant and g value of a particular J manifold of the free ion). There are two other reported measurements for Np⁴⁺ in various crystals or molecules, $4,16$ and these ratios are given in Table IV along with the present value obtained for $\texttt{Np}^\texttt{4+}$ in ZrSiO $_\texttt{4}$. The ground state wavefunction obtained from the optical fit shows that the ground state is -97% pure J = *9/2.* Therefore, this ratio should represent a check on the validity of the present data. The agreement between the earlier *alg* ratios and the B/g value obtained in this work are considered to be satisfactory. The experimental uncertainties in A and g_{\parallel} , however, are too great to apply this test.

VI. Discussion

The zircon structure is representative of a class of tetragonal crystals that includes ThSiO_h, HfSiO_h, ZrSiO_h, YPO_h and the heavier lanthanide ortho phosphates, vanadates, and arsenates. The metal ion is located at a site of D_{2d} symmetry surrounded by eight oxygen atoms in a dodecahedral array. The S_{μ} axis of the metal atom site is parallel to the optic axis of the crystal.¹⁷⁻¹⁹ $2r^{4+}$ has an eight-coordinate ionic radius of 0.84A while the eight-coordinated ionic radius of Th⁴⁺ is 1.05A.²⁰ Thus, when a Np⁴⁺ ion substitutes for a $2r^{4+}$ ion, a movement of the surrounding atoms away from the impurity ion is expected. For ThSiO_n, however, the Np⁴⁺ impurity ion should cause much less distortion. Furthermore, the crystal-field interaction experienced by the Np⁴⁺ ion will be larger in ZrSiO₄ than in ThSiO₄.

Table VII lists the parameters for those actinide ions in ZrSiO_{μ} and ThSiO_{μ} whose optical spectra have been analyzed. It is reassuring to note that the crystal-field parameters for U^{4+} :ZrSiO_h and Np⁴⁺:ZrSiO_h are very similar. The crystal-field parameters for Np $^{\natural+}$:ZrSiO₄ are quite different and much larger than those for Np^{4+} :ThSiO_n. This is indicative of the much larger crystal field found in the $2rSiO_\mu$ host as shown qualitatively by the Auzel parameter $\frac{21}{\gamma}$ N_V/(4 π)^{1/2} that is also listed in Table VII.

For r^n ions where n is odd, the selection rules are not very restrictive. The present analysis is essentially based on crystal-field parameters obtained from the $\texttt{U}^\mathfrak{4}$:ZrSiO $_\mathfrak{q}$ analysis. With the use of these 4+ parameters and the Np free-ion parameters resulting from the barameters obtained from the U^{μ} : ZrSiO₄ analysis. With the parameters and the Np⁴⁺ free-ion parameters resulting from 4^{4+} : Zr(BD₄)₄ analysis, it was possible to assign 31 Np⁴⁺ Np^{4+} :Zr(BD₁₁)₁ analysis, it was possible to assign 31 Np⁴⁺ energy levels rather easily, and adjustment of'the parameters as described earlier led to a very good value for o. It is rather disturbing, however, that 13 other transitions of comparable intensity and with good polarization characteristics led to an increased rms deviation of ~100 cm^{-1} . A number of fits were attempted with various starting parameters, but these resulted in the inversion of several Γ_6 and Γ_7 levels without producing a significant decrease in o. The resulting parameters from the 31 level fit, however, were used to calculate the rms deviation for all of the observed strong tansitions.

The reason for the above discrepancy is not understood at present. The absorption lines were very broad, and the line width did not decrease markedly in the dilute crystal. It is possible that more than one Np site is present in these crystals that could be responsible for the observed large line widths and the noted marked deviations in the

fit for some levels. Additionally, impurities can arise from the flux used in the crystal growth process. Unfortunately, however, it is difficult to explore a variety of growth conditions when radioactive materials are employed.

Although the free-ion parameters for Np^{4+} :ZrSiO_n were obtained over a small energy range and must be considered to be rather tentative, the ratios of the parameters given in Table VII, that have been defined by Rajnak et al.,⁴ are consistent with the observations in that work. All of the $\text{NP}^{\downarrow +}$:ZrSiO_{μ} ratios indicate decreasing covalency with increasing atomic number as compared to the results for $\texttt{U}^{\natural+}$ in ZrSiO $_\texttt{4}$. It should be noted, however, that there is increased scatter when the corresponding ratios are compared for U^{4+} and Np⁴⁺ in the ThSiO_h host.

VII. Conclusion

The optical spectrum of NP^{4+} :ZrSiO_n has been analyzed with 31 strong transitions assigned using crystal-field parameters consistent with those determined previously for $\texttt{U}^{\texttt{4+}}$:ZrSiO $_\texttt{4}$. Thirteen other relatively intense levels did not fit well. EPR results confirmed the assignment of the ground crystal-field state of $\mathtt{Np}^{\natural +}$ in ZrSiO $_\mathtt{L}$. A comparison of the empirical parameters obtained for Np $^{4+}$:ZrSiO $_{\textrm{\tiny{H}}}$ with those obtained for the $\texttt{U}^{\texttt{4+}}$:ZrSiO₄ shows the same trends as those found in comparing the parameters of NP^{4+} :Zr(BD_H)_H with those of U^{4+} :Hf(BD_h)_h^{4,22} i.e., covalency effects are found to decrease with increasing atomic number.

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Table I. Absorption spectra of Np^{4+} /ZrSiO₄

 a VS, very strong; S, strong; M, medium; W, weak; vw, very weak; hsh., shoulder

 $^{\circ}$ These transitions were not assigned.

These transitions were assigned but not used in the fitting procedure.

Table III. Spin-Hamiltonian parameters for Np $^{4+}$ /ZrSiO₄

* Calculated from the wavefunctions obtained from fitting the optical

spectra.

 ϵ

Table IV. Ratios of the hyperfine coupling constants and g values.

 \mathcal{L}

Table V. Final parameter values of Np^{4+} : ZrSiO₄ (all parameters in

 a Values of the parameters in [] are fixed as in Reference 4.

 σ^{C}

 b n is the no. of levels; values in { } are for 44 assigned levels with the above parameters.

$$
c_{\sigma} = \left(\frac{\sum (E_{\text{calc}} - E_{\text{exp}})}{n - p}\right)^2
$$
 where E_{calc} and E_{exp} are the calculated and
experimental energies and p is the number of free parameters.

Table VI. Calculated and experimental energy levels

 $\ddot{}$

 $7 \quad 11940.6$ $19.5\frac{2}{19.5\frac{1}{19.5\frac{1}{19.2}} + 14.6\frac{2}{19.2}}$ 29.7% 2 H(2)_{9/2} + 18.0% 2 G(1)_{9/2} 26.7% ⁴ $G_{5/2}$ + 16.7% ⁴ $F_{5/2}$ 65.9% $4 - 2$

16 17814.4 17869.0 ;':'54.6* 43.6% ⁴ *F3/2 +* 2 12.3% - *H(2)9/2* 32.0% 2 H(2)_{11/2} + 18.3% ⁴G_{11/2} $39.4\frac{2}{11/2} + 17.1\frac{4}{11/2}$ $-$ 2 $+$ *26.7% K13/2* + 7.7% *³ 3/2* 58.7% ²K_{13/2} + 8.3% ²G(1)_{7/2} 48.7% $^{4}G_{9/2}$ + 11.3% $^{4}D_{5/2}$ 45.7% $4^{4}G_{9/2}$ + 7.8% $4^{4}D_{5/2}$ 29.0% 4 G_{9/2} + 10.0% 4 D_{5/2}

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6 21714.0 21728.0 -14.0 34.8%⁴G_{9/2} + 15.9%²G(1)_{7/2} -26.3% $^{4}G_{9/2}$ + 12.0% $^{2}G(1)_{7/2}$ 21.1% $^{4}D_{5/2}$ + 17.0% $^{2}D(2)_{5/2}$ $K_{15/2}$ + 16.8% L_{15/2} 20.9% ${}^{4}D_{3/2}$ + 12.0% ${}^{2}D(1)_{3/2}$ 24.6% 2 H(1)_{11/2} + 11.7% 2 D(1)_{5/2} 37.7% ²H(1)_{11/2} + 12.4%²I_{11/2} 15.4% $^{2}D(1)_{5/2}$ + 13.6% $^{2}K_{15/2}$ 21.8% $^{4}G_{11/2}$ + 14.1% $^{2}D(1)_{5/2}$

* These thirteen levels were assigned but were not used in the fitting procedure. See text.

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\frac{N_v}{(\frac{u_\pi}{1/2})^{1/2}}
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Figure Captions

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- Figure 1. Polarized absorption spectra of the 1 wt % Np^{4+} :ZrSiO₄ at 4.2K in the 20000-7800 A (2000-780 nm) range.
- Figure 2. Polarized absorption spectra of the 1 wt % Np^{4+} :ZrSiO₄ in the 7800-3400 A (780-340 nm) range.

ABSORBANCE (arbitrary unit)

XBL 875-2412

ABSORBANCE (orbitrary unit

XBL 875-2413

Figure 2

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L4WRENCE BERKELEY L4BORATORY TECHNICAL INFORMATION DEPARTMENT UNIVERSITY OF CALIFORNIA BERKELEY, CALIFORNIA 94720

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 $\label{eq:2.1} \frac{1}{2} \sum_{i=1}^n \frac{1}{2} \sum_{i=1}^n \frac{1}{2} \sum_{j=1}^n \frac{1}{2} \sum_{i=1}^n \frac{1}{2} \sum_{i=1}^n \frac{1}{2} \sum_{j=1}^n \frac{$